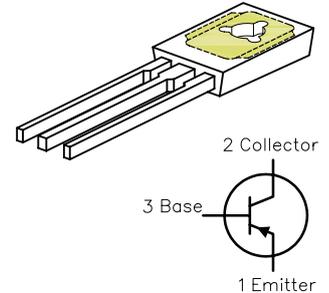




**RoHS  
Compliant**



### Description:

Silicon TO-126 PNP Power Transistor for use in power amplifier and switching excellent safe area limits.

### Absolute Maximum Ratings:

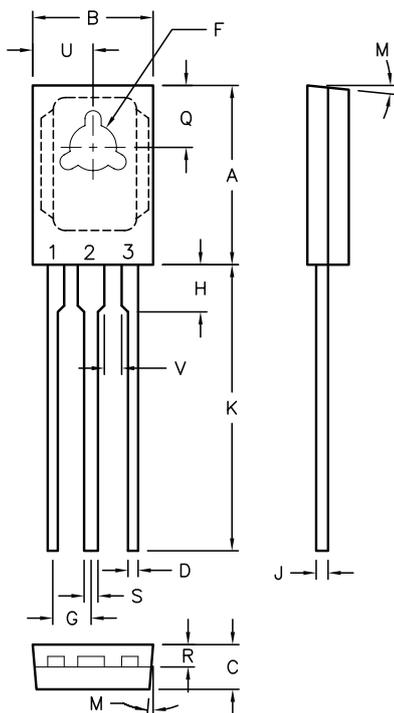
Characteristic	Symbol	Rating
Collector - Base Voltage	$V_{CBO}$	80V
Collector - Emitter Voltage	$V_{CEO}$	80V
Emitter - Base Voltage	$V_{EBO}$	5V
Continuous Collector Current	$I_C$	4A
Base Current	$I_B$	1A
Total Device Dissipation ( $T_c = +25^\circ\text{C}$ ) Derate above $25^\circ\text{C}$	$P_D$	40W 320mW/ $^\circ\text{C}$
Operating Junction Temperature Range	$T_J$	$-65^\circ\text{C}$ to $+150^\circ\text{C}$
Storage Temperature Range	$T_{STG}$	$-65^\circ\text{C}$ to $+150^\circ\text{C}$

### Electrical Characteristics ( $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min.	Max.	Unit
<b>OFF Characteristics</b>					
Collector - Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 100\text{mA}$ , $I_B = 0$ (Note1)	80	-	V
Collector Cut-off Current	$I_{CEO}$	$V_{CE} = 80\text{V}$ , $I_E = 0$	-	1	mA
	$I_{CBX}$	$V_{CE} = 80\text{V}$ , $V_{EB(off)} = 1.5\text{V}$	-	0.1	mA
	$I_{CEO}$	$V_{CE} = 80\text{V}$ , $I_E = 0$	-	0.1	mA
Emitter Cut-off Current	$I_{EBO}$	$V_{EB} = 5\text{V}$ , $I_C = 0$	-	1	mA
<b>ON Characteristics (Note 1)</b>					
DC Current Gain	$h_{FE}$	$V_{CE} = 2\text{V}$ , $I_C = 1.5\text{A}$	20	80	-
		$V_{CE} = 2\text{V}$ , $I_C = 4\text{A}$	7	-	-
Collector - Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 1.5\text{A}$ , $I_B = 0.15\text{mA}$	-	0.6	V
		$I_C = 4\text{A}$ , $I_B = 1\text{A}$	-	1.4	V
Base - Emitter On Voltage	$V_{BE(on)}$	$I_C = 1.5\text{A}$ , $V_{CE} = 2\text{V}$	-	1.2	V

Parameter	Symbol	Test Conditions	Min.	Max.	Unit
<b>Small-Signal Characteristics</b>					
Current Gain - Bandwidth Product	$f_T$	$V_{CE} = 10V, I_c = 1A, f = 1MHz$	2	-	MHz

Note 1 : Pulse test : Pulse width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$



**Pin Configuration:**

1. Emitter
2. Collector
3. Base

Dim.	Min.	Max.
A	10.8	11.05
B	7.49	7.75
C	2.41	2.67
D	0.51	0.66
F	2.92	3.18
G	2.31	2.46
H	1.27	2.41
J	0.38	0.64
K	15.11	16.64
M	3° TYP	
Q	3.76	4.01
R	1.14	1.4
S	0.64	0.89
U	3.68	3.94
V	1.02	-

Dimensions : Millimetres

**Part Number Table**

Description	Part Number
Bipolar Transistor, PNP, 4A, 80V, TO-126	2N5195

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